

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- **High-Frequency Operation**
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

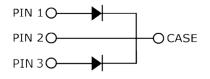
- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters





Part Number	Package	Qty(PCS)		
HFFSH10120ADN-F155	TO247-3L	30		

TO247-3L **Package**



Maximum Ratings (T_c=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V _{RSM}	Surge Peak Reverse Voltage	1300	V		
V _R	DC Peak Reverse Voltage	1200	V		
I _F	Continuous Forward Current (Per Leg/Device)	19/38 9/18 5/10	А	T _c =25°C T _c =135°C T _c =160°C	Fig. 3
I _{FRM}	Repetitive Peak Forward Surge Current	26* 18*	А	T _c =25°C, t _P =10 ms, Half Sine Pulse T _c =110°C, t _P =10 ms, Half Sine Pulse	
I _{FSM}	Non-Repetitive Forward Surge Current	46* 36*	А	T_c =25°C, t_p =10 ms, Half Sine Pulse T_c =110°C, t_p =10 ms, Half Sine Pulse	Fig. 8
I _{F,Max}	Non-Repetitive Peak Forward Current	400* 320*	А	T_c =25°C, t_p =10 ms, Pulse T_c =110°C, t_p =10 ms, Pulse	Fig. 8
P _{tot}	Power Dissipation(Per Leg/Device)	93/187 40/81	w	T _c =25°C T _c =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-650V	
∫i²dt	i²t value	10.6* 6.5*	A²s	T _c =25°C, t _p =10 ms T _c =110°C, t _p =10 ms	
TJ	Operating Junction Range	-55 to +175	°C		
T _{stg}	Storage Temperature Range	-55 to +135	°C		
	TO-247 Mounting Torque	1 8.8	Nm Ibf-in	M3 Screw 6-32 Screw	

^{*} Per Leg, ** Per Device



Electrical Characteristics (Per Leg)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.4 1.9	1.8 3	V	I _F = 5 A T _J =25°C I _F = 5 A T _J =175°C	Fig. 1
I _R	Reverse Current	20 40	150 300	μΑ	V _R = 1200 V T _J =25°C V _R = 1200 V T _J =175°C	Fig. 2
Q _c	Total Capacitive Charge	27		nC	$V_R = 800 \text{ V, } I_F = 5A$ $di/dt = 200 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	Fig. 5
С	Total Capacitance	390 27 20		pF	V _R = 0 V, T _J = 25°C, f = 1 MHz V _R = 400 V, T _J = 25°C, f = 1 MHz V _R = 800 V, T _J = 25°C, f = 1 MHz	Fig. 6
E _c	Capacitance Stored Energy	8.0		μJ	V _R = 800 V	Fig. 7

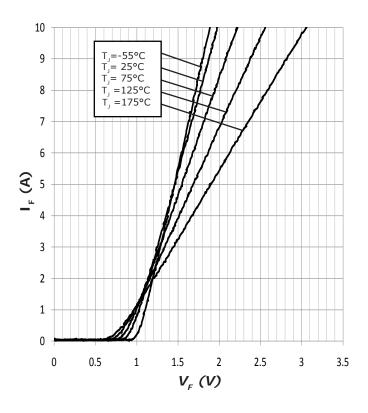
Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Тур.	Unit	Note
R _{eJC}	Thermal Resistance from Junction to Case	1.6* 0.8**	°C/W	Fig. 9

^{*} Per Leg, ** Per Device

Typical Performance (Per Leg)





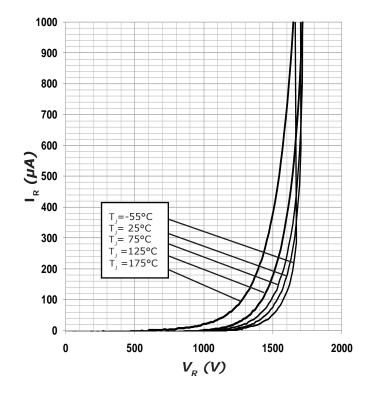


Figure 2. Reverse Characteristics



Typical Performance (Per Leg)

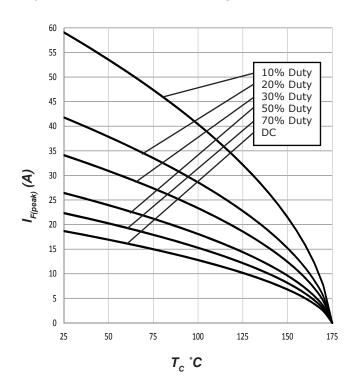


Figure 3. Current Derating

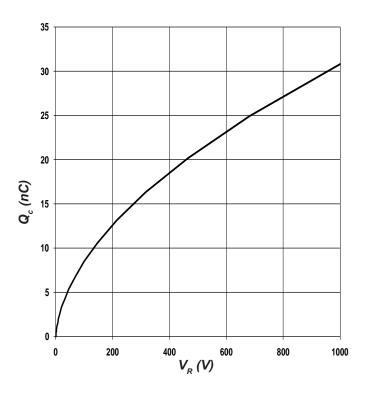


Figure 5. Recovery Charge vs. Reverse Voltage

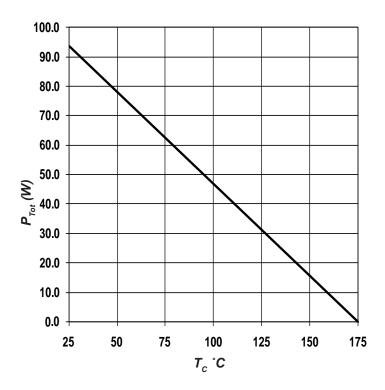


Figure 4. Power Derating

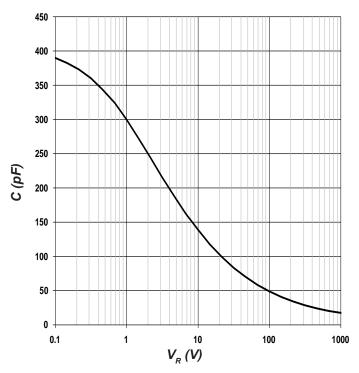
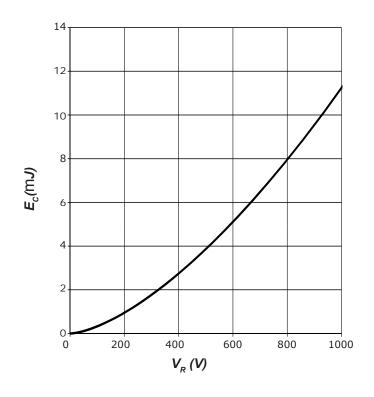


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance



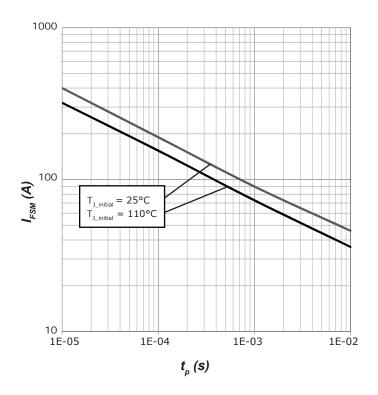


Figure 7. Typical Capacitance Stored Energy, per leg

Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform), per leg

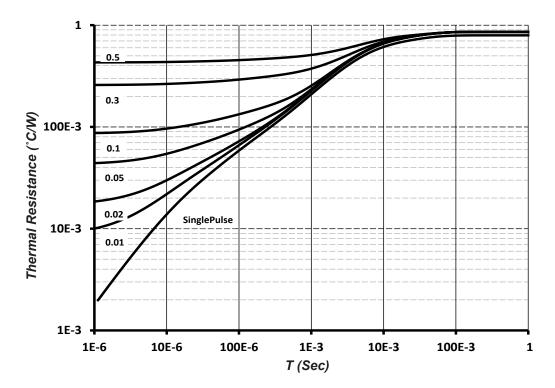
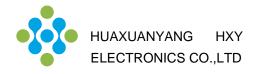


Figure 9. Device Transient Thermal Impedance



Diode Model

$$Vf_{T} = V_{T} + If * R_{T}$$

$$V_{T} = 0.96 + (T_{j} * -1.22*10^{-3})$$

$$R_{T} = 0.08 + (T_{j} * 8.5*10^{-4})$$

$$V_{T} = 0.08 + (T_{j} * 8.5*10^{-4})$$

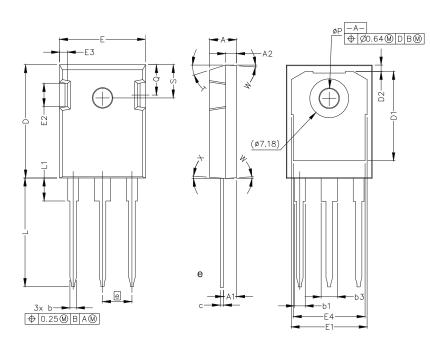
Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

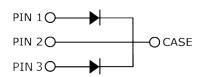
HFFSH10120ADN-F155

Silicon Carbide Schottky Diode

Package Dimensions

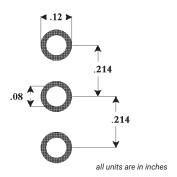
Package TO247-3L





POS	Inc	hes	Millimeters		
P03	Min	Max	Min	Max	
А	.190	.205	4.83	5.21	
A1	.090	.100	2.29	2.54	
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b1	.075	.095	1.91	2.41	
b3	.113	.133	2.87	3.38	
С	.022	.027	0.55	0.68	
D	.819	.831	20.80	21.10	
D1	.640	.695	16.25	17.65	
D2	.037	.049	0.95	1.25	
Е	.620	.635	15.75	16.13	
E1	.516	.557	13.10	14.15	
E2	.145	.201	3.68	5.10	
E3	.039	.075	1.00	1.90	
E4	.487	.529	12.38	13.43	
е	.214	BSC	5.44 BSC		
L	.780	.800	19.81	20.32	
L1	.161	.173	4.10	4.40	
N	3				
ØP	.138	.144	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	
Т	17.5° REF				
W	3.5° REF				
Х	4° REF				

Recommended Solder Pad Layout



HFFSH10120ADN-F155

Silicon Carbide Schottky Diode

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